

1 (currently amended). A method for hermetically sealing of dielectrically
 2 insulating isolation trenches by filling with a fill material in a deposition method,
 3 wherein each of the trenches has a first width (b1) and is ~~are~~ slightly
 4 broadened (b2) at a specific positions (2) and trench portion longitudinally
 5 adjacent to the first width, wherein a low pressure deposition technique is
 6 used such that a void channels (5) forming is formed in the an area of the
 7 each trenches having ~~normal~~ the first width (b1) by closing the an upper trench
 8 portions with the a fill material (9) are ~~and~~ hermetically sealed each trench in
 9 ~~the a~~ longitudinal direction ~~of the trench by means of~~ by low pressure material
 10 deposition from the broadened trench portion and along the length direction of
 11 ~~the~~ each trench.

2(cancelled).

1 3(previously presented). The method of claim 1, wherein the broadened
 2 trench portions are provided in regular intervals.

4(cancelled).

1 5(currently amended). A method for hermetically sealing
 2 dielectrically insulating isolation trenches by filling with a low pressure
 3 deposition technique,

4 (i) wherein ~~the each~~ isolation trenches ~~are~~ has two portions of a first
 5 width, both being slightly broadened towards at least ~~at least at~~ one specific
 6 position broader trench portion that is longitudinally between the two
 7 portions of the first width;

8 (ii) a said low pressure deposition technique is used to hermetically seal
 9 a void in a longitudinal direction of the isolation trench by ~~means of a~~ said low
 10 pressure material deposition starting from the at least one broadened trench

portion ~~(2, 3)~~ and along ~~the~~ a length direction of the trench, wherein said void ~~is~~
was formed in ~~the area of the~~ each isolation trenches ~~(4)~~ portion having the
 normal first width and due to the closure of the upper trench portions of first
width with said fill material.

6(cancelled).

7(previously presented). The method of claim 5, wherein a plurality of
 broadened trench portions are provided in regular intervals for forming sealing
 positions along a channel.

8(previously presented). The method of claim 5, wherein the slightly
 broadened isolation trenches are broadened at the at least at one position
 according to a width that is not greater than the width of the trench at the non-
 broadened position.

9(currently amended). The method of claim 5, wherein ~~the~~ each
 broadened ing trench portion (2, 3) is provided by two conical sections ~~(3)~~,
starting from the first width portions of each trench.

10(previously presented). The method of claim 5, wherein the low
 pressure technique is performed substantially at vacuum conditions.

11(previously presented). The method of claim 5, wherein the
 broadening is provided at least at a short piece compared to the total length of
 the channel.

12(currently amended). The method of claim 5, wherein the selection of
 parameters of the deposition process and of a trench configuration is performed
 such that possibly remaining lateral voids are completely sealed before the

~~slightly broadened trench section having the slight broadening (b2) portion is~~
~~closed in the an upwards direction, so that a inhibiting further filling cannot~~
~~take place of the trench.~~

13(currently amended). A device comprising a wafer having formed
 therein isolation trenches, said wafer including hermetically sealed dielectrically
 insulating isolation trenches formed by filling with a low pressure deposition
 method,

(i) wherein ~~the each~~ isolation trenches ~~(1, 2) are is~~ slightly broadened
 at least at one specific ~~position~~ portion between at least two conical portions
towards two portions of a smaller width than said broadened width;

(ii) wherein void channels are hermetically sealed in the longitudinal
 direction of ~~the each~~ trench by ~~a said~~ low pressure material deposition from the
 broadened trench portion in the longitudinal direction of the trench filled by
 means of ~~a the~~ low pressure deposition technique, said void channels ~~being~~
~~having~~ formed during the filling in ~~the area of~~ the trenches having the ~~normal~~
smaller width by closing the upper trench portions with fill material.

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